


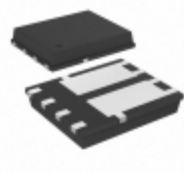

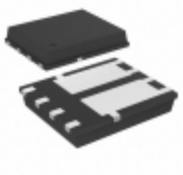
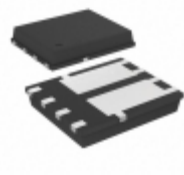

	<p>SI7844DP-T1-E3</p>
	<p>Hersteller-Teilenummer: SI7844DP-T1-E3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET 2N-CH 30V 6.4A PPAK SO-8</p> <p>Datenblätter:  SI7844DP-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 93250 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7844DP-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET 2N-CH 30V 6.4A PPAK SO-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	93250 pcs Stock
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	1.4W
Verpackung / Gehäuse	PowerPAK® SO-8 Dual
Supplier Device-Gehäuse	PowerPAK® SO-8 Dual
Typ FET	2 N-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	6.4A
Rds On (Max) @ Id, Vgs	22 mOhm @ 10A, 10V
VGS (th) (Max) @ Id	2.4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	20nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Original-Reel®































SI7844DP-T1-E3 ist neu im Original, Suche SI7844DP-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7844DP-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7844DP-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 SI7846DP VISHAY SI7846DP VISHAY	 SI7844DP-T1 VISHAY SI7844DP-T1 VISHAY	 SI7844DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 30V 6.4A PPAK SO-8	 SI7842DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 30V 6.3A PPAK SO-8
 SI7842DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 30V 6.3A PPAK SO-8	 SI7842DP-T1-GE3 Vishay / Siliconix MOSFET 2N-CH 30V 6.3A PPAK SO-8	 SI7844DP-T1-GE3 Vishay / Siliconix MOSFET 2N-CH 30V 6.4A PPAK SO-8	 SI7844DP-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 30V 6.4A PPAK SO-8

heiße Teile

Mehr

 SI7812DN-T1-GE3	 SI7818DN-T1-E3	 SI7818DN-T1-E3	 SI7820DN-T1-E3	 SI7820DN-T1-E3
 SI7820DN-T1-GE3	 SI7820DN-T1-GE3	 SI7840BDP	 SI7840BDP-T1-E3	 SI7840BDP-T1-E3
 SI7840BDP-T1-GE3	 SI7840BDP-T1-GE3	 SI7840DP	 SI7840DP-T1	 SI7840DP-T1-E3
 SI7840DP-T1-GE3	 SI7840DP-T1-GE3	 SI7842DP	 SI7842DP-T1-E3	 SI7842DP-T1-E3
 SI7842DP-T1-GE3	 SI7842DP-T1-GE3	 SI7844DP	 SI7844DP-T1	 SI7844DP-T1-E3
 SI7844DP-T1-GE3	 SI7844DP-T1-GE3	 SI7846DP	 SI7846DP-T1-E3	 SI7846DP-T1-E3
 SI7846DP-T1-GE3	 SI7846DP-T1-GE3	 SI7846DP-TI	 SI7846SAC	 SI7848BDP-T1-E3
 SI7848BDP-T1-E3	 SI7848BDP-T1-GE3	 SI7848BDP-T1-GE3	 SI7848DP	 SI7848DP-T1-E3
 SI7848DP-T1-E3	 SI7848DP-T1-GE3	 SI7850DP	 SI7850DP-T1-E3	 SI7850DP-T1-E3
 SI7850DP-T1-GE3	 SI7850DP-T1-GE3	 SI7852ADP	 SI7852ADP-T1-E3	 SI7852ADP-T1-E3

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